Toshio Kamiya

List of Publications by Year
in descending order

418 papers	35,240 citations	84 h-index (4960)	181 g-index (3579)
441 all docs	441 docs citations	441 times ranked	16308 citing authors

#	Article	IF	Citations
1	Room-temperature fabrication of transparent flexible thin-film transistors using amorphous oxide semiconductors. Nature, 2004, 432, 488-492.	27.8	6,503
2	Thin-Film Transistor Fabricated in Single-Crystalline Transparent Oxide Semiconductor. Science, 2003, 300, 1269-1272.	12.6	1,709
3	Present status of amorphous Inâ€"Gaâ€"Znâ€"O thin-film transistors. Science and Technology of Advanced Materials, 2010, 11, 044305.	6.1	1,559
4	Iron-Based Layered Superconductor:Â LaOFeP. Journal of the American Chemical Society, 2006, 128, 10012-10013.	13.7	1,207
5	High-mobility thin-film transistor with amorphous InGaZnO4 channel fabricated by room temperature rf-magnetron sputtering. Applied Physics Letters, 2006, 89, 112123.	3.3	1,048
6	Material characteristics and applications of transparent amorphous oxide semiconductors. NPG Asia Materials, 2010, 2, 15-22.	7.9	852
7	High-Density Electron Anions in a Nanoporous Single Crystal: [Ca24Al28O64]4+(4e-). Science, 2003, 301, 626-629.	12.6	744
8	Amorphous Oxide Semiconductors for High-Performance Flexible Thin-Film Transistors. Japanese Journal of Applied Physics, 2006, 45, 4303-4308.	1.5	659
9	p -channel thin-film transistor using p-type oxide semiconductor, SnO. Applied Physics Letters, 2008, 93, .	3.3	577
10	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping. Journal of Display Technology, 2009, 5, 273-288.	1.2	464
11	Light-induced conversion of an insulating refractory oxide into a persistent electronic conductor. Nature, 2002, 419, 462-465.	27.8	431
12	Carrier transport and electronic structure in amorphous oxide semiconductor, a-InGaZnO4. Thin Solid Films, 2005, 486, 38-41.	1.8	423
13	Fabrication and photoresponse of a pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO and n-ZnO. Applied Physics Letters, 2003, 83, 1029-1031.	3.3	329
14	Origins of threshold voltage shifts in room-temperature deposited and annealed a-Inâ€"Gaâ€"Znâ€"O thin-film transistors. Applied Physics Letters, 2009, 95, .	3.3	324
15	Modeling of amorphous InGaZnO4 thin film transistors and their subgap density of states. Applied Physics Letters, 2008, 92, .	3.3	318
16	Subgap states in transparent amorphous oxide semiconductor, Inâ€"Gaâ€"Znâ€"O, observed by bulk sensitive x-ray photoelectron spectroscopy. Applied Physics Letters, 2008, 92, .	3.3	298
17	Trap densities in amorphous-InGaZnO4 thin-film transistors. Applied Physics Letters, 2008, 92, .	3.3	290
18	Defect passivation and homogenization of amorphous oxide thin-film transistor by wet O2 annealing. Applied Physics Letters, 2008, 93, .	3.3	276

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19	Local coordination structure and electronic structure of the large electron mobility amorphous oxide semiconductor In-Ga-Zn-O: Experiment and<i>ab initio</i>calculations. Physical Review B, 2007, 75, .	3.2	275
20	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping*. Journal of Display Technology, 2009, 5, 468-483.	1.2	272
21	Nickel-Based Oxyphosphide Superconductor with a Layered Crystal Structure, LaNiOP. Inorganic Chemistry, 2007, 46, 7719-7721.	4.0	268
22	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides <i>M</i>CuO<i>Ch</i> (<i>M</i> = Bi, La; <i>Ch</i> = S, Se, Te): Effects of Electronic Configurations of <i>M</i>³⁺ Ions. Chemistry of Materials, 2008, 20, 326-334.	6.7	258
23	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO3(ZnO)5 films. Applied Physics Letters, 2004, 85, 1993-1995.	3.3	247
24	Advantageous grain boundaries in iron pnictide superconductors. Nature Communications, 2011, 2, 409.	12.8	246
25	Ambipolar Oxide Thinâ€Film Transistor. Advanced Materials, 2011, 23, 3431-3434.	21.0	236
26	Epitaxial growth of high mobility Cu2O thin films and application to p-channel thin film transistor. Applied Physics Letters, 2008, 93, .	3.3	222
27	Combinatorial approach to thin-film transistors using multicomponent semiconductor channels: An application to amorphous oxide semiconductors in Inâ€"Gaâ€"Znâ€"O system. Applied Physics Letters, 2007, 90, 242114.	3.3	219
28	Electronic Structures Above Mobility Edges in Crystalline and Amorphous In-Ga-Zn-O: Percolation Conduction Examined by Analytical Model. Journal of Display Technology, 2009, 5, 462-467.	1.2	219
29	Electronic structure of oxygen deficient amorphous oxide semiconductor aâ€InGaZnO_{4â€"<i>x</i>}: Optical analyses and firstâ€principle calculations. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3098-3100.	0.8	214
30	Tin monoxide as an sâ€orbitalâ€based pâ€type oxide semiconductor: Electronic structures and TFT application. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2187-2191.	1.8	213
31	Work Function of a Roomâ€Temperature, Stable Electride [Ca₂₄Al₂₈O₆₄]⁴⁺(e^{â€"})₄. Advanced Materials, 2007, 19, 3564-3569.	21.0	209
32	Metallic State in a Limeâˆ'Alumina Compound with Nanoporous Structure. Nano Letters, 2007, 7, 1138-1143.	9.1	208
33	Electronic structure of the amorphous oxide semiconductor aâ€InGaZnO_{4â€"<i>x</i>}: Taucâ€"Lorentz optical model and origins of subgap states. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 860-867.	1.8	207
34	UV-detector based on pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO/n-ZnO. Thin Solid Films, 2003, 445, 317-321.	1.8	206
35	Effects of excess oxygen on operation characteristics of amorphous In-Ga-Zn-O thin-film transistors. Applied Physics Letters, 2011, 99, .	3.3	203
36	Specific contact resistances between amorphous oxide semiconductor Inâ€"Gaâ€"Znâ€"O and metallic electrodes. Thin Solid Films, 2008, 516, 5899-5902.	1.8	191

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37	Effects of Diffusion of Hydrogen and Oxygen on Electrical Properties of Amorphous Oxide Semiconductor, In-Ga-Zn-O. ECS Journal of Solid State Science and Technology, 2013, 2, P5-P8.	1.8	191
38	Intrinsic defects in a photovoltaic perovskite variant Cs₂SnI₆. Physical Chemistry Chemical Physics, 2015, 17, 18900-18903.	2.8	191
39	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. Applied Physics Letters, 2010, 97, .	3.3	189
40	Electronic Defects in Amorphous Oxide Semiconductors: A Review. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800372.	1.8	179
41	Field Emission of Electron Anions Clathrated in Subnanometer-Sized Cages in [Ca24Al28O64]4+(4e-). Advanced Materials, 2004, 16, 685-689.	21.0	175
42	Growth, structure and carrier transport properties of Ga2O3 epitaxial film examined for transparent field-effect transistor. Thin Solid Films, 2006, 496, 37-41.	1.8	173
43	Amorphous Inâ€“Gaâ€“Znâ€“O coplanar homojunction thin-film transistor. Applied Physics Letters, 2009, 94, 133502.	3.3	168
44	Degenerate p-type conductivity in wide-gap LaCuOS1â^’xSex (x=0â€“1) epitaxial films. Applied Physics Letters, 2003, 82, 1048-1050.	3.3	166
45	Amorphous oxide channel TFTs. Thin Solid Films, 2008, 516, 1516-1522.	1.8	166
46	Factors controlling electron transport properties in transparent amorphous oxide semiconductors. Journal of Non-Crystalline Solids, 2008, 354, 2796-2800.	3.1	162
47	Highly stable amorphous In-Ga-Zn-O thin-film transistors produced by eliminating deep subgap defects. Applied Physics Letters, 2011, 99, .	3.3	156
48	A p-Type Amorphous Oxide Semiconductor and Room Temperature Fabrication of Amorphous Oxide pâ€“n Heterojunction Diodes. Advanced Materials, 2003, 15, 1409-1413.	21.0	154
49	Depth analysis of subgap electronic states in amorphous oxide semiconductor, a-In-Ga-Zn-O, studied by hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2011, 109, 073726.	2.5	151
50	Two-Dimensional Transition-Metal Electride Y₂C. Chemistry of Materials, 2014, 26, 6638-6643.	6.7	151
51	Proton Conduction in In[sup 3+]-Doped SnP[sub 2]O[sub 7] at Intermediate Temperatures. Journal of the Electrochemical Society, 2006, 153, A1604.	2.9	149
52	Subgap states, doping and defect formation energies in amorphous oxide semiconductor aâ€InGaZnO₄ studied by density functional theory. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1698-1703.	1.8	149
53	Bipolar Conduction in SnO Thin Films. Electrochemical and Solid-State Letters, 2011, 14, H13.	2.2	148
54	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. Applied Physics Letters, 2010, 96, .	3.3	139

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55	Itinerant ferromagnetism in the layered crystals<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>LaCoO</mml:mtext><mml:mi>X</mml:mi><mml:mspace width="0.3em" /><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mi>X</mml:mi><mml:mo>=</mml:mo><mml:mtext>P</mml:mtext><mml:mo Physical Review B, 2008, 77, .	3.2	138
56	Field-induced current modulation in epitaxial film of deep-ultraviolet transparent oxide semiconductor Ga2O3. Applied Physics Letters, 2006, 88, 092106.	3.3	137
57	Ligand-Hole in [SnI6] Unit and Origin of Band Gap in Photovoltaic Perovskite Variant Cs2SnI6. Bulletin of the Chemical Society of Japan, 2015, 88, 1250-1255.	3.2	130
58	Frontier of transparent oxide semiconductors. Solid-State Electronics, 2003, 47, 2261-2267.	1.4	129
59	Circuits using uniform TFTs based on amorphous Inâ€Gaâ€Znâ€O. Journal of the Society for Information Display, 2007, 15, 915-921.	2.1	121
60	Fabrication and characterization of heteroepitaxial p-n junction diode composed of wide-gap oxide semiconductors p-ZnRh2O4/n-ZnO. Applied Physics Letters, 2003, 82, 823-825.	3.3	119
61	Nickel-based phosphide superconductor with infinite-layer structure, BaNi2P2. Solid State Communications, 2008, 147, 111-113.	1.9	118
62	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. Applied Physics Letters, 2013, 103, .	3.3	112
63	Transparent amorphous oxide semiconductors for organic electronics: Application to inverted OLEDs. Proceedings of the National Academy of Sciences of the United States of America, 2017, 114, 233-238.	7.1	111
64	Fast Thin-Film Transistor Circuits Based on Amorphous Oxide Semiconductor. IEEE Electron Device Letters, 2007, 28, 273-275.	3.9	110
65	Biaxially textured cobalt-doped BaFe2As2 films with high critical current density over 1â€,MA/cm2 on MgO-buffered metal-tape flexible substrates. Applied Physics Letters, 2011, 98, 242510.	3.3	110
66	Characteristics of optical guided modes in multilayer metal-clad planar optical guide with low-index dielectric buffer layer. IEEE Journal of Quantum Electronics, 1975, 11, 729-736.	1.9	104
67	Superconductivity in Epitaxial Thin Films of Co-Doped SrFe2As2with Bilayered FeAs Structures and their Magnetic Anisotropy. Applied Physics Express, 2008, 1, 101702.	2.4	103
68	Bandgap Optimization of Perovskite Semiconductors for Photovoltaic Applications. Chemistry - A European Journal, 2018, 24, 2305-2316.	3.3	103
69	Room temperature nanocrystalline silicon single-electron transistors. Journal of Applied Physics, 2003, 94, 633-637.	2.5	102
70	Nickel-based layered superconductor, LaNiOAs. Journal of Solid State Chemistry, 2008, 181, 2117-2120.	2.9	99
71	Femtosecond-laser-encoded distributed-feedback color center laser in lithium fluoride single crystals. Applied Physics Letters, 2004, 84, 311-313.	3.3	97
72	Single-atomic-layered quantum wells built in wide-gap semiconductorsLnCuOCh(Ln=lanthanide,Ch=chalcogen). Physical Review B, 2004, 69, .	3.2	97

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73	Intermediate-Temperature Proton Conduction in Al[sup 3+]-Doped SnP[sub 2]O[sub 7]. Journal of the Electrochemical Society, 2007, 154, B1265.	2.9	95
74	Electrical and Optical Properties and Electronic Structures of LnCuOS (Ln = Laâˆ¼Nd). Chemistry of Materials, 2003, 15, 3692-3695.	6.7	94
75	Electric field-induced superconducting transition of insulating FeSe thin film at 35 K. Proceedings of the National Academy of Sciences of the United States of America, 2016, 113, 3986-3990.	7.1	93
76	Heavy hole doping of epitaxial thin films of a wide gap p-type semiconductor, LaCuOSe, and analysis of the effective mass. Applied Physics Letters, 2007, 91, .	3.3	91
77	Heteroepitaxial growth and optoelectronic properties of layered iron oxyarsenide, LaFeAsO. Applied Physics Letters, 2008, 93, 162504.	3.3	91
78	Three-dimensionally stacked flexible integrated circuit: Amorphous oxide/polymer hybrid complementary inverter using n-type a-Inâ€“Gaâ€“Znâ€“O and p-type poly-(9,9-dioctylfluorene-co-bithiophene) thin-film transistors. Applied Physics Letters, 2010, 96, .	3.3	91
79	Structural relaxation in amorphous oxide semiconductor, a-In-Ga-Zn-O. Journal of Applied Physics, 2012, 111, .	2.5	90
80	Diffusion-Limited a-IGZO/Pt Schottky Junction Fabricated at 200 $^{circ}hbox{C}$ on a Flexible Substrate. IEEE Electron Device Letters, 2011, 32, 1695-1697.	3.9	89
81	Conversion of an ultra-wide bandgap amorphous oxide insulator to a semiconductor. NPG Asia Materials, 2017, 9, e359-e359.	7.9	89
82	A germanate transparent conductive oxide. Nature Communications, 2011, 2, 470.	12.8	88
83	Wide-gap layered oxychalcogenide semiconductors: Materials, electronic structures and optoelectronic properties. Thin Solid Films, 2006, 496, 8-15.	1.8	86
84	Electron field emission from TiO2 nanotube arrays synthesized by hydrothermal reaction. Applied Physics Letters, 2006, 89, 043114.	3.3	84
85	Device characteristics improvement of a-Inâ€“Gaâ€“Znâ€“O TFTs by low-temperature annealing. Thin Solid Films, 2010, 518, 3017-3021.	1.8	84
86	High Critical Current Density 4 MA/cm²in Co-Doped BaFe₂As₂Epitaxial Films Grown on (La,Sr)(Al,Ta)O₃Substrates without Buffer Layers. Applied Physics Express, 2010, 3, 063101.	2.4	83
87	(Invited) Roles of Hydrogen in Amorphous Oxide Semiconductor. ECS Transactions, 2013, 54, 103-113.	0.5	82
88	Intense thermal field electron emission from room-temperature stable electride. Applied Physics Letters, 2005, 87, 254103.	3.3	81
89	Intrinsic excitonic photoluminescence and band-gap engineering of wide-gapp-type oxychalcogenide epitaxial films of LnCuOCh (Ln=La, Pr, and Nd; Ch=S or Se) semiconductor alloys. Journal of Applied Physics, 2003, 94, 5805-5808.	2.5	79
90	Stability and high-frequency operation of amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors with various passivation layers. Thin Solid Films, 2012, 520, 3778-3782.	1.8	78

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91	Electronic Structure of Oxygen Dangling Bond in GlassySiO2: The Role of Hyperconjugation. Physical Review Letters, 2003, 90, 186404.	7.8	76
92	Electron Confinement in Channel Spaces for One-Dimensional Electride. Journal of Physical Chemistry Letters, 2015, 6, 4966-4971.	4.6	74
93	Improved coupled mode analysis of corrugated waveguides and lasers. IEEE Journal of Quantum Electronics, 1978, 14, 245-258.	1.9	73
94	Fabrication of Highly Conductive 12CaOÂ·7Al2O3 Thin Films Encaging Hydride Ions by Proton Implantation. Advanced Materials, 2003, 15, 1100-1103.	21.0	72
95	Electronic Structures and Device Applications of Transparent Oxide Semiconductors: What Is the Real Merit of Oxide Semiconductors?. International Journal of Applied Ceramic Technology, 2005, 2, 285-294.	2.1	72
96	First-principles study of native point defects in crystalline indium gallium zinc oxide. Journal of Applied Physics, 2009, 105, .	2.5	72
97	Electromagnetic properties and electronic structure of the iron-based layered superconductor LaFePO. Physical Review B, 2008, 77, .	3.2	70
98	Water-induced superconductivity inSrFe2As2. Physical Review B, 2009, 80, .	3.2	69
99	Interface and bulk effects for biasâ€"lightâ€illumination instability in amorphousâ€Inâ€"Gaâ€"Znâ€"O thinâ€film transistors. Journal of the Society for Information Display, 2010, 18, 789-795.	2.1	69
100	Photoelectron Spectroscopic Study of C12A7:e-and Alq3Interface:â€‰ The Formation of a Low Electron-Injection Barrier. Journal of Physical Chemistry C, 2007, 111, 8403-8406.	3.1	68
101	Znâ€"Inâ€"O based thinâ€film transistors: Compositional dependence. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1915-1919.	1.8	68
102	Josephson junction in cobalt-doped BaFe2As2 epitaxial thin films on (La,Sr)(Al,Ta)O3 bicrystal substrates. Applied Physics Letters, 2010, 96, .	3.3	68
103	Atomically-flat, chemically-stable, superconducting epitaxial thin film of iron-based superconductor, cobalt-doped. Solid State Communications, 2009, 149, 2121-2124.	1.9	66
104	Effects of postâ€annealing on (110) Cu₂O epitaxial films and origin of low mobility in Cu₂O thinâ€film transistor. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2192-2197.	1.8	65
105	Large Photoresponse in Amorphous Inâ€"Gaâ€"Znâ€"O and Origin of Reversible and Slow Decay. Electrochemical and Solid-State Letters, 2010, 13, H324.	2.2	62
106	n-type conversion of SnS by isovalent ion substitution: Geometrical doping as a new doping route. Scientific Reports, 2015, 5, 10428.	3.3	59
107	Holographic writing of volume-type microgratings in silica glass by a single chirped laser pulse. Applied Physics Letters, 2002, 81, 1137-1139.	3.3	58
108	Growth mechanism for single-crystalline thin film of InGaO3(ZnO)5 by reactive solid-phase epitaxy. Journal of Applied Physics, 2004, 95, 5532-5539.	2.5	58

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109	Electrical Properties and Structure of p-Type Amorphous Oxide SemiconductorxZnOÂ·Rh2O3. Advanced Functional Materials, 2005, 15, 968-974.	14.9	58
110	Optical and Carrier Transport Properties of Cosputtered Znâ€“Inâ€“Snâ€“O Films and Their Applications to TFTs. Journal of the Electrochemical Society, 2008, 155, H390.	2.9	57
111	Amorphous Inâ€“Gaâ€“Zn-O thin-film transistor with coplanar homojunction structure. Thin Solid Films, 2009, 518, 1309-1313.	1.8	57
112	Third-order optical nonlinearity originating from room-temperature exciton in layered compounds LaCuOS and LaCuOSe. Applied Physics Letters, 2004, 84, 879-881.	3.3	56
113	Localized and Delocalized Electrons in Room-Temperature Stable Electride [Ca₂₄Al₂₈O₆₄]⁴⁺(O²⁻)₂₋<i>_x</i>(<i>e</i>… Analysis of Optical Reflectance Spectra. Journal of Physical Chemistry C, 2008, 112, 4753-4760.	8.1	56
114	42.1: <i>Invited Paper</i>: Improved Amorphous Inâ€Gaâ€Znâ€O TFTs. Digest of Technical Papers SID International Symposium, 2008, 39, 621-624.	0.3	56
115	Simple Analytical Model of On Operation of Amorphous Inâ€“Gaâ€“Znâ€“O Thin-Film Transistors. IEEE Transactions on Electron Devices, 2011, 58, 3463-3471.	3.0	56
116	Mechanism for Heteroepitaxial Growth of Transparent P-Type Semiconductor:â€‰ LaCuOS by Reactive Solid-Phase Epitaxy. Crystal Growth and Design, 2004, 4, 301-307.	3.0	54
117	Pâ€13: Photosensitivity of Amorphous IGZO TFTs for Activeâ€Matrix Flatâ€Panel Displays. Digest of Technical Papers SID International Symposium, 2008, 39, 1215-1218.	0.3	54
118	Calculation of Crystal Structures, Dielectric Constants and Piezoelectric Properties of Wurtzite-Type Crystals Using Ab-Initio Periodic Hartree-Fock Method. Japanese Journal of Applied Physics, 1996, 35, 4421-4426.	1.5	53
119	Excitonic blue luminescence from p-LaCuOSeâˆ•n-InGaZn5O8 light-emitting diode at room temperature. Applied Physics Letters, 2005, 87, 211107.	3.3	53
120	Amorphous Inâ€“Gaâ€“Znâ€“O Dual-Gate TFTs: Currentâ€“Voltage Characteristics and Electrical Stress Instabilities. IEEE Transactions on Electron Devices, 2012, 59, 1928-1935.	3.0	53
121	High electron doping to a wide band gap semiconductor 12CaOâˆ™7Al2O3 thin film. Applied Physics Letters, 2007, 90, 182105.	3.3	52
122	Formation of inorganic electride thin films via site-selective extrusion by energetic inert gas ions. Journal of Applied Physics, 2005, 97, 023510.	2.5	51
123	Intrinsic carrier mobility in amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors determined by combined field-effect technique. Applied Physics Letters, 2010, 96, 262105.	3.3	51
124	Thin film fabrication of nano-porous 12CaOÂ·7Al2O3 crystal and its conversion into transparent conductive films by light illumination. Thin Solid Films, 2003, 445, 309-312.	1.8	50
125	Opto-electronic properties and light-emitting device application of widegap layered oxychalcogenides: LaCuOCh(Ch= chalcogen) and La2CdO2Se2. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2800-2811.	1.8	50
126	Comprehensive studies on the stabilities of a-In-Ga-Zn-O based thin film transistor by constant current stress. Thin Solid Films, 2010, 518, 3012-3016.	1.8	50

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127	Thin Film Growth and Device Fabrication of Iron-Based Superconductors. Journal of the Physical Society of Japan, 2012, 81, 011011.	1.6	50
128	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. ECS Journal of Solid State Science and Technology, 2014, 3, Q3085-Q3090.	1.8	50
129	Low Threshold Voltage and Carrier Injection Properties of Inverted Organic Light-Emitting Diodes with [Ca₂₄Al₂₈O₆₄]⁴⁺(4e^{â^'}) Cathode and Cu_{2â^'<i>x</i>}Se Anode. Journal of Physical Chemistry C, 2009, 113, 18379-18384.	3.1	49
130	Route to <i>n</i>-type doping in SnS. Applied Physics Letters, 2015, 106, .	3.3	49
131	Antiferromagnetic bipolar semiconductor LaMnPO with ZrCuSiAs-type structure. Journal of Applied Physics, 2009, 105, 093916.	2.5	47
132	DC superconducting quantum interference devices fabricated using bicrystal grain boundary junctions in Co-doped BaFe₂As₂epitaxial films. Superconductor Science and Technology, 2010, 23, 082001.	3.5	47
133	Electride and superconductivity behaviors in Mn5Si3-type intermetallics. Npj Quantum Materials, 2017, 2, .	5.2	47
134	Device applications of transparent oxide semiconductors: Excitonic blue LED and transparent flexible TFT. Journal of Electroceramics, 2006, 17, 267-275.	2.0	46
135	Operation Characteristics of Thin-Film Transistors Using Very Thin Amorphous Inâ€"Gaâ€"Znâ€"O Channels. Electrochemical and Solid-State Letters, 2011, 14, H197.	2.2	46
136	Growth, structure, and transport properties of thin (>10 nm) n-type microcrystalline silicon prepared on silicon oxide and its application to single-electron transistor. Journal of Applied Physics, 2001, 89, 6265-6271.	2.5	45
137	Field-Induced Current Modulation in Nanoporous Semiconductor, Electron-Doped 12CaOÂ·7Al2O3. Chemistry of Materials, 2005, 17, 6311-6316.	6.7	45
138	ZnO-Based Semiconductors as Building Blocks for Active Devices. MRS Bulletin, 2008, 33, 1061-1066.	3.5	45
139	Electron effective mass and mobility limits in degenerate perovskite stannate<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>BaSnO</mml:mi><mml:mn>3</mml:mn></mml:msub></ Physical Review B, 2017, 95, .	3.2	45
140	EPR identification of two types of carbon vacancies in4Hâ^'SiC. Physical Review B, 2004, 69, .	3.2	43
141	Origins of Hole Doping and Relevant Optoelectronic Properties of Wide Gap p-Type Semiconductor, LaCuOSe. Journal of the American Chemical Society, 2010, 132, 15060-15067.	13.7	43
142	High critical-current density with less anisotropy in BaFe2(As,P)2 epitaxial thin films: Effect of intentionally grown <i>c</i>-axis vortex-pinning centers. Applied Physics Letters, 2014, 104, .	3.3	43
143	Photoluminescence from Au ion-implanted nanoporous single-crystal12CaOâˆ™7Al2O3. Physical Review B, 2006, 73, .	3.2	42
144	Identical effects of indirect and direct electron doping of superconducting BaFe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>As<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>thin films. Physical Review B, 2012, 85, .	3.2	42

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145	Role of lone pair electrons in determining the optoelectronic properties of BiCuOSe. Physical Review B, 2012, 85, .	3.2	42
146	Thin film growth by pulsed laser deposition and properties of 122-type iron-based superconductor AE(Fe_{1âˆ’<i>x</i>}Co_{<i>x</i>})₂As₂(AE=alkaline earth). Superconductor Science and Technology, 2012, 25, 084015.	3.5	42
147	Wide gap p-type degenerate semiconductor: Mg-doped LaCuOSe. Thin Solid Films, 2003, 445, 304-308.	1.8	41
148	Temperature dependence of single-event transient current induced by heavy-ion microbeam on p/sup +//n/n/sup +/ epilayer junctions. IEEE Transactions on Nuclear Science, 2004, 51, 2834-2839.	2.0	40
149	Heteroepitaxial growth of layered semiconductors, LaZnOPn (Pn=P and As). Thin Solid Films, 2008, 516, 5800-5804.	1.8	40
150	Doping effects in amorphous oxides. Journal of the Ceramic Society of Japan, 2012, 120, 447-457.	1.1	40
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